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|---|---|----|-----|------------------------|----------------------|--|--|
|   |   |    |     | Application Number     | TBA                  |  |  |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT |   |    |     | Filing Date            | Filed Herewith       |  |  |
|   |   |    |     | First Named Inventor   | William F. Seng      |  |  |
| <b>0</b> 17                                   |   |    |     | Art Unit               | TBD                  |  |  |
| (use as many sheets as necessary)             |   |    |     | Examiner Name          | TBD                  |  |  |
| Sheet   | ı | of | · 1 | Attorney Docket Number | 90065.001090/8018.00 |  |  |

|                      |              | OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS   |    |
|----------------------|--------------|---|----|
| Examiner<br>Initials | Cite<br>No.1 | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T2 |
| do                   | 1            | "Interface Chemistry and Electrical Properties of Annealed Ni and Ni/Al-6H SiC Structures", C. Halling, R. Yakimova, V. Krastev, Ts. Marinova and E. Janzen, Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.   |    |
| M                    | 2            | "The Influence of Dry Cleaning Techniques on Thermal Oxides Grown on 4H and 6H P-type SiC", CM. Zetterling, C.I. Harris, M. Ostling and V.V. Afanas'ev", Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.   |    |
| W                    | 3            | "Specific Contact Resistance as a Function of Doping N-type 4H and 6H-SiC", Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.  |    |
| Na                   | 4            | "Aluminum Doped 6H SiC: CVD Growth and Formation of Ohmic Contacts", Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.   |    |
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